



Study of gain of LGAD

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Gain Characterization

Use of a low-noise Charge Sensitive pre-amplifier (Amptek A250) to determine the gain of several families of LGADs exposed to different radiation sources (⁹⁰Sr, ²⁴¹Am, ⁵⁵Fe, Alphas).

In this presentation, OLD BNL LGAD (shallow gain implant), new BNL LGAD (deeper implant), HPK (deep gain implant) - we submitted a paper on NIM (soon on arxiv.org)

All BNL fabricated LGAD/AC-LGAD will undergo the same tests.

Betas from ⁹⁰Sr

BNL 3045 - Sr - PX5 Gain = 5





Gamma rays from ²⁴¹Am







X rays from ⁵⁵Fe

Fe 55 - w3045





Alphas from ²⁴¹Am







Gain

Easy calibration with PIN diode or with C_{inj} (2.1pF)

Max gain for betas: effects of charge cloud shape clearly visible







Spectroscopic parameters (⁵⁵Fe)





Laser Tests

Searching for effects of gain saturation in LGADs hit by laser

- scan in laser threshold
- Scan in voltage
- Diode and LGAD coming from same wafer
- FNAL board

Mip generates charge along small radius track and instantaneously

VS

Laser focused at 15um and signal \sim 350ps long at high threshold (longer at lower threshold). \rightarrow Laser track is order of magnitudes less dense.

Still, interesting to see saturation effects with laser injection. A lot of data acquired so far, still interpreting them. Much more soon.

